

Form PTO 1449  
(Modified)U.S. DEPARTMENT OF COMMERCE  
PATENT AND TRADEMARK OFFICE

ATTY DOCKET NO.

215686US99CIP

SERIAL NO.

09/985,757

## LIST OF REFERENCES CITED BY APPLICANT

APPLICANT

Fred RICHARD, et al.

FILING DATE

November 6, 2001

GROUP

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## U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
AA	3,802,967	04/09/74	Ladany et al.			
AB	4,174,422	11/13/79	Mathews et al.			
AC	4,404,265	09/13/83	Manasevit			
AD	4,482,906	11/13/84	Hovel et al.			
AE	4,523,211	06/11/85	Morimoto et al.			
AF	4,661,176	04/28/87	Manasevit			
AG	4,793,872	12/27/88	Meunier et al.			
AH	4,846,926	07/11/89	Kay et al.			
AJ	4,855,249	08/08/89	Akasaki et al.			
AI	4,891,091	01/02/90	Shastry			
AK	4,912,087	03/27/90	Aslam et al.			
AL	4,928,154	05/22/90	Umeno et al.			
AM	4,963,949	10/16/90	Wanlass et al.			
AN	5,141,894	08/25/92	Bisaro et al.			
AO	5,159,413	10/27/92	Calviello et al.			
AP	5,173,474	12/22/92	Connell et al.			
AQ	5,221,367	06/22/93	Chisholm et al.			
AR	5,225,031	07/06/93	McKee et al.			
AS	5,358,925	10/25/94	Neville Connell et al.			
AT	5,393,352	02/28/95	Summerfelt			
AU	5,418,216	05/23/95	Fork			
AV	5,450,812	09/19/95	McKee et al.			
AW	5,478,653	12/26/95	Guenzer			
AX	5,482,003	01/09/96	McKee et al.			
AY	5,514,484	05/07/96	Nashimoto			
AZ	5,556,463	09/17/96	Guenzer			
BA	5,588,995	12/31/96	Sheldon			
BB	5,670,798	09/23/97	Schetzina			
BC	5,733,641	03/31/98	Fork et al.			
BD	5,735,949	04/07/98	Manti et al.			
BE	5,741,724	04/21/98	Ramdani et al.			
BF	5,810,923	09/22/98	Yano et al.			
BG	5,830,270	11/03/98	McKee et al.			
BH	5,912,068	06/15/99	Jia			
BI	6,020,222	02/01/00	Wollesen			
BJ	6,045,626	04/04/00	Yano et al.			
BK	6,064,078	05/16/00	Northrup et al.			
BL	6,064,092	05/16/00	Park			
BM	6,096,584	08/01/00	Ellis-Monaghan et al.			
BN	6,103,008	08/15/00	McKee et al.			
BO	6,136,666	10/24/00	So			
BP	6,174,755	01/16/01	Manning			



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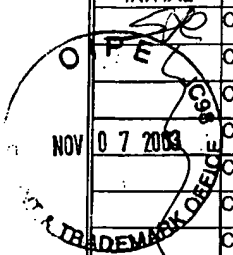
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## U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
CA		3,766,370	10/16/73	Walther			
CB		4,006,989	02/08/77	Andringa			
CC		4,284,329	08/18/81	Smith et al.			
CD		4,777,613	10/11/98	Shahan et al.			
CE		4,802,182	01/31/89	Thomton et al.			
CF		4,882,300	11/21/89	Inoue et al.			
CG		4,896,194	01/23/90	Suzuki			
CH		4,999,842	03/12/91	Huang et al.			
CI		5,081,062	01/14/92	Vasudev et al.			
CJ		5,155,658	10/13/92	Inam et al.			
CK		5,248,564	09/28/93	Ramesh			
CL		5,260,394	11/09/93	Tazaki et al.			
CM		5,270,298	12/14/93	Ramesh			
CN		5,286,985	02/15/94	Taddiken			
CO		5,310,707	05/10/94	Oishi et al.			
CP		5,326,721	07/05/94	Summerfelt			
CQ		5,404,581	04/04/95	Honjo			
CR		5,418,389	05/23/95	Watanabe			
CS		5,436,759	07/25/95	Dijali et al.			
CT		5,576,879	11/19/96	Nashimoto			
CU		5,606,184	02/25/97	Abrokwhah, et al.			
CV		5,640,267	06/17/97	May et al.			
CW		5,674,366	10/07/97	Hayashi et al.			
CX		5,729,641	03/17/98	Chandonnet et al.			
CY		5,790,583	08/04/98	Ho			
CZ		5,825,799	10/20/98	Ho et al.			
DA		5,857,049	01/05/99	Beranek et al.			
DB		5,874,860	02/23/99	Brunel et al.			
DC		5,926,496	07/20/99	Ho et al.			
DD		5,937,285	08/10/99	Abrokwhah, et al.			
DE		5,981,400	11/09/99	Lo			
DF		5,990,495	11/23/99	Ohba			
DG		6,002,375	12/14/99	Corman et al.			
DH		6,008,762	12/28/99	Nghiem			
DI		6,055,179	04/25/00	Koganei et al.			
DJ		6,107,653	08/22/00	Fitzgerald			
DK		6,113,690	09/05/00	Yu et al.			
DL		6,114,996	09/05/00	Nghiem			
DM		6,121,642	09/19/00	Newns			
DN		6,128,178	10/03/00	Newns			
DO		6,143,072	11/07/00	McKee et al.			



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EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
EA		4,484,332	11/20/84	Hawrylo			
EB		4,815,084	03/21/89	Scifres et al.			
EC		4,876,219	10/24/89	Eshita et al.			
ED		4,963,508	10/16/90	Umeno et al.			
EE		5,060,031	10/22/91	Abrokwah, et al.			
EF		5,063,166	11/05/91	Mooney et al.			
EG		5,116,461	05/26/92	Lebby et al.			
EH		5,127,067	06/30/92	Delcoco et al.			
EI		5,144,400	09/01/92	Ma			
EJ		5,293,050	03/08/94	Chapple-Sokol et al			
EK		5,356,831	10/18/94	Calviello et al.			
EL		5,391,515	02/21/95	Kao et al.			
EM		5,442,191	08/15/95	Ma			
EN		5,444,016	08/22/95	Abrokwah, et al.			
EO		5,480,829	01/02/96	Abrokwah, et al.			
EP		5,528,414	06/18/96	Oakley			
EQ		5,614,739	03/25/97	Abrokwah et al.			
ER		5,729,394	03/17/98	Sevier et al.			
ES		5,731,220	03/24/98	Tsu et al.			
ET		5,764,676	06/09/98	Paoli et al.			
EU		5,777,762	07/07/98	Yamamoto			
EV		5,778,018	07/07/98	Yoshikawa et al.			
EW		5,778,116	07/07/98	Tomich			
EX		5,801,105	09/01/98	Yano et al.			
EY		5,828,080	10/27/98	Yano et al.			
EZ		5,858,814	01/12/99	Goossen et al.			
FA		5,861,966	01/19/99	Ortel			
FB		5,883,996	03/16/99	Knapp et al.			
FC		5,995,359	11/30/99	Klee et al.			
FD		6,058,131	05/02/00	Pan			
FE		6,137,603	10/24/00	Henmi			
FF		6,146,906	11/14/00	Inoue et al.			
FG		6,173,474	01/16/01	Conrad			
FH		6,180,252	01/30/01	Farrell et al.			
FI		4,242,595	12/30/0	Lehovec			
FJ		4,398,342	08/16/83	Pitt et al.			
FK		4,424,589	01/03/84	Thomas et al.			
FL		4,876,208	10/24/89	Gustafson et al.			
FM		4,482,422	11/84	McGinn et al.			
FN		4,667,088	05/19/87	Kramer			
FO		4,772,929	09/20/88	Manchester et al.			
FP		4,841,775	06/27/89	Ikeda et al.			

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EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	GA	4,868,376	09/19/89	Lessin et al.			
	GB	4,885,376	12/05/89	Verkade			
	GC	4,888,202	12/89	Murakami et al.			
	GD	4,891,091	12/90	Wanlass et al.			
	GE	5,051,790	09/24/91	Hammer			
	GF	5,055,445	10/08/91	Belt et al.			
	GG	5,081,519	11/14/92	Nishimura et al.			
	GH	5,143,854	09/01/92	Pirung et al.			
	GI	5,185,589	02/09/93	Krishnaswamy et al.			
	GJ	5,191,625	03/02/93	Gustavsson			
	GK	5,194,397	03/16/93	Cook et al.			
	GL	5,208,182	05/04/93	Narayan et al.			
	GM	5,216,729	06/01/93	Berger et al.			
	GN	5,314,547	05/24/94	Heremans et al.			
	GO	5,352,926	10/04/94	Andrews			
	GP	5,356,509	10/18/94	Terranova et al.			
	GQ	5,371,734	12/06/94	Fischer			
	GR	5,372,992	12/94	Itozaki et al.			
	GS	5,405,802	04/11/95	Yamagata et al.			
	GT	5,442,561	08/15/95	Yoshizawa et al.			
	GU	5,453,727	09/26/95	Shibasaki et al.			
	GV	5,466,631	11/14/95	Ichikawa et al.			
	GW	5,473,047	12/05/95	Shi			
	GX	5,473,171	12/95	Summerfelt			
	GY	5,479,033	12/26/95	Baca et al.			
	GZ	5,486,406	01/23/96	Shi			
	HA	5,491,461	02/13/96	Partin et al.			
	HB	5,492,859	02/20/96	Sakaguchi et al.			
	HC	5,494,711	02/27/96	Takeda et al.			
	HD	5,504,035	04/02/96	Rostoker et al.			
	HE	5,504,183	04/02/96	Shi			
	HF	5,511,238	04/23/96	Bayraktaroglu			
	HG	5,512,773	04/96	Wolf et al.			
	HH	5,515,047	05/07/96	Yamakido et al.			
	HI	5,515,810	05/14/96	Yamashita et al.			
	HJ	5,519,235	05/96	Ramesh			
	HK	5,549,977	08/96	Jin et al.			
	HL	5,551,238	09/03/96	Prueitt			
	HM	5,552,547	09/03/96	Shi			
	HN	5,589,284	12/31/96	Summerfelt et al.			
	HO	5,602,418	02/11/97	Imai et al.			
	HP	5,633,724	05/27/97	King et al.			

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LIST OF REFERENCES CITED BY APPLICANT				APPLICANT Fred RICHARD, t al.			
				FILING DATE November 6, 2001		GROUP 2811	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
O T P E NOV 07 2003 PATA TRADEMARK OFFICE	IA	5,650,646	07/22/97	Summerfelt			
	IB	5,656,382	08/12/97	Nashimoto			
	IC	5,659,180	08/19/97	Shen et al.			
	ID	5,661,112	08/26/97	Hatta et al.			
	IE	5,679,965	11/95	Schetzina			
	IF	5,725,641	03/10/98	MacLeod			
	IG	5,745,631	04/28/98	Reinker			
	IH	5,776,621	07/07/98	Nashimoto			
	II	5,777,350	07/07/98	Nakamura et al.			
	IJ	5,789,845	08/04/98	Wadaka et al.			
	IK	5,792,569	08/11/98	Sun et al.			
	IL	5,792,679	08/11/98	Nakato			
	IM	5,796,648	08/18/98	Kawakubo et al.			
	IN	5,801,072	09/01/98	Barber			
	IO	5,812,272	09/22/98	King et al.			
	IP	5,814,583	09/98	Itozaki et al.			
	IQ	5,825,055	10/20/98	Summerfelt			
	IR	5,827,755	10/27/98	Yonchara et al.			
	IS	5,833,603	11/10/98	Kovacs et al.			
	IT	5,838,035	11/17/98	Ramesh			
IU	5,844,260	12/01/98	Ohori				
IV	5,846,846	12/08/98	Suh et al.				
IW	5,863,326	01/26/99	Nause et al.				
IX	5,872,493	02/16/99	Ella				
IY	5,879,956	03/99	Seon et al.				
IZ	5,880,452	03/09/99	Plesko				
JA	5,883,564	03/16/99	Partin				
JB	5,907,792	05/25/99	Droopad et al.				
JC	5,937,274	08/10/99	Kondow et al.				
JD	5,948,161	09/07/99	Kizuki				
JE	5,959,879	09/28/99	Koo				
JF	5,966,323	10/99	Chen et al.				
JG	5,987,011	11/16/99	Toh				
JH	6,022,140	02/08/00	Fraden et al.				
JI	6,022,410	02/08/00	Yu et al.				
JJ	6,023,082	02/08/00	McKee et al.				
JK	6,028,853	02/22/00	Haartsen				
JL	6,049,702	04/11/00	Tham et al.				
JM	6,078,717	06/20/00	Nashimoto et al				
JN	6,088,216	07/00	Laibowitz et al.				
JO	6,090,659	07/00	Laibowitz et al.				
JP	6,107,721	08/22/00	Lakin				

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LIST OF REFERENCES CITED BY APPLICANT				APPLICANT Fred RICHARD, et al.			
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U.S. PATENT DOCUMENTS							
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE	
KA	6,153,454	11/28/00	Krivokapic				
KB	6,191,011	02/01	Gilboa et al				
KC	6,204,737	03/20/01	Ella				
KD	6,224,669	05/01/01	Yi et al.				
KE	6,225,051	05/01/01	Sugiyama et al.				
KF	6,241,821	06/05/01	Yu et al.				
KG	6,265,749	07/24/01	Gardner et al.				
KH	6,313,486	11/01	Kencke et al.				
KI	6,316,832	11/13/01	Tsuzuki et al.				
KJ	2002/0008234	01/02	Emrick				
KK	3,670,213	06/13/72	Nakawaga et al.				
KL	4,756,007	07/05/88	Qureshi et al.				
KM	4,773,063	09/20/88	Hunsperger et al.				
KN	5,394,489	02/28/95	Koch				
KO	5,406,202	04/11/95	Mehrgardt et al.				
KP	5,528,067	06/18/96	Farb et al.				
KQ	5,572,052	11/05/96	Kashihara et al.				
KR	5,767,543	06/16/98	Ooms et al.				
KS	6,175,497	01/16/01	Tseng et al.				
KT	6,197,503	03/06/01	Vo-Dinh et al.				
KU	6,248,459	06/19/01	Wang et al.				
KV	6,252,261	06/26/01	Usui et al.				
KW	6,255,198	07/03/01	Linthicum et al.				
KX	6,268,269	07/31/01	Lee et al.				
KY	6,291,319	09/18/01	Yu et al.				
KZ	6,316,785	11/13/01	Nunoue et al.				
LA	6,343,171	01/29/02	Yoshimura et al.				
LB	4,965,649	10/23/90	Zanio et al.				
LC	6,253,649	05/01	Kawahara et al.				
LD	6,211,096	04/01	Allman et al.				
LE	6,239,449	05/29/01	Fafard et al.				
LF	2001/0013313	08/16/01	Droopad et al.				
LG	6,184,044	02/06/01	Sone et al.				
LH	6,011,646	01/04/00	Mirkarimi et al.				
LI	5,227,196	07/13/93	Itoh				
LJ	6,150,239	11/21/00	Goesele et al.				
LK	5,441,577	08/15/95	Sasaki et al.				
LL	4,459,325	07/10/84	Nozawa et al.				
LM	4,392,297	07/12/83	Little				
LN	4,289,920	09/15/81	Hovel				
LO	5,281,834	01/25/94	Cambou et al.				

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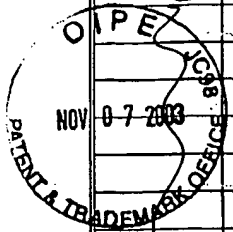
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MA	5,553,089	09/03/96	Seki et al.				
MB	5,528,057	06/18/96	Yanagase et al.				
MC	6,229,159	05/08/01	Suzuki				
MD	4,748,485	05/31/88	Vasudev				
ME	4,984,043	01/08/91	Vinal				
MF	5,754,319	05/19/98	Van De Voorde et al.				
MG	6,108,125	08/22/00	Yano				
MH	5,073,981	12/17/91	Giles et al.				
MI	5,140,651	08/18/92	Soref et al.				
MJ	5,610,744	03/11/97	Ho et al.				
MK	6,362,017	03/26/02	Manabe et al.				
ML	6,242,686	06/05/01	Kishimoto et al.				
MM	5,689,123	11/18/97	Major et al.				
MN	5,670,800	09/23/97	Nakao et al.				
MO	5,067,809	11/26/91	Tsubota				
MP	5,596,205	01/21/97	Reedy et al.				
MQ	6,175,555	01/16/01	Hoole				
MR	5,357,122	10/18/94	Okubora et al.				
MS	4,084,130	04/11/78	Holton				
MT	6,093,302	07/25/00	Montgomery				
MU	6,372,813	04/16/02	Johnson et al.				
MV	5,608,046	03/04/97	Cook et al.				
MW	5,955,591	09/21/99	Imbach et al.				
MX	6,022,963	02/08/00	McGall et al.				
MY	6,083,697	07/04/00	Beecher et al.				
MZ	5,063,081	11/05/91	Cozzette et al.				
NA	5,479,317	12/26/95	Ramesh				
NB	5,306,649	04/26/94	Hebert				
NC	5,962,069	10/05/99	Schindler et al.				
ND	5,541,422	07/30/96	Wolf et al.				
NE	5,873,977	02/23/99	Desu et al.				
NF	5,538,941	07/23/96	Findikoglu et al.				
NG	6,046,464	04/04/00	Schetzina				
NH	6,235,145	05/22/01	Li et al.				
NI	5,610,744	03/11/97	Ho et al.				
NJ	5,280,013	01/18/94	Newman et al.				
NK	6,348,373 B1	02/19/02	Ma et al.				
NL	8,339,664 B1	01/15/02	Farjady et al.				
NM	4,439,014	03/27/84	Stacy et al.				
NN	4,889,402	12/26/89	Reinhart				
NO	5,963,291	10/05/99	Wu et al.				
NP	6,011,641	01/04/00	Shin et al.				
NQ	6,340,788 B1	01/22/02	King et al.				



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U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
O P F NOV 07 2003 U.S. PATENT AND TRADEMARK OFFICE - BOSTON	OA	5,807,440	09/15/98	Kubota et al.			
	OB	4,681,982	07/21/87	Yoshida			
	OC	4,629,821	12/16/86	Bronstein-Bonte et al.			
	OD	4,452,720	06/05/84	Harada et al.			
	OE	3,935,031	01/27/76	Adler			
	OF	5,760,426	06/02/98	Marx et al.			
	OG	5,053,835	10/01/91	Horikawa et al.			
	OH	6,326,645 B1	12/04/01	Kadota			
	OI	5,770,887	06/23/98	Tadatomo et al.			
	OJ	6,372,356 B1	04/16/02	Thornton et al.			
	OK	4,774,205	09/27/88	Choi et al.			
	OL	6,359,330 B1	03/19/02	Goudard			
	OM	5,312,765	05/17/94	Kanber			
	ON	5,734,672	03/31/98	McMinn et al.			
	OO	6,367,699 B2	04/09/02	Ackley			
	OP	5,530,235	06/25/96	Stefik et al.			
	OQ	5,623,552	04/22/97	Lane			
	OR	5,481,102	01/02/96	Hazelrigg, Jr.			
	OS	6,134,114	10/17/00	Ungermann et al.			
	OT	5,984,190	11/16/99	Nevill			
	OU	5,789,733	08/04/98	Jachimowicz et al.			
	OV	5,753,300	05/19/98	Wessels et al.			
	OW	6,208,453	03/27/01	Wessels et al.			
	OX	5,886,867	03/23/99	Chivukula et al.			
	OY	5,028,976	07/02/91	Ozaki et al.			
	OZ	5,869,845	02/09/99	Vander Wagt et al.			
	PA	5,596,214	01/21/97	Endo			
	PB	6,391,674 B2	05/21/02	Ziegler			
	PC	6,275,122 B1	08/14/01	Speidell et al.			
	PD	6,238,946 B1	05/29/01	Ziegler			
PE	6,210,988 B1	04/03/01	Howe et al.				
PF	6,392,257	05/21/02	Ramdani et al.				
PG	4,442,590	04/17/84	Stockton et al.				
PH	5,603,764	02/18/97	Matsuda et al.				
PI	6,087,681	06/11/00	Shakuda				
PJ	5,132,648	07/21/92	Trinh et al.				
PK	6,427,066	07/30/02	Grube				
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QB		5,599,953	10/29/96	Kikkawa et al.			
QC		5,834,362	11/10/98	Miyagaki et al.			
QD		6,248,621 B1	06/19/01	Wilk et al.			
QE		5,266,355	11/30/93	Wernberg et al.			
QF		6,277,436 B1	08/21/01	Stauf et al.			
QG		6,039,803	03/21/00	Fitzgerald et al.			
QH		5,619,051	04/08/97	Endo			
QI		5,420,102	05/30/95	Harshavardhan et al.			
QJ		5,210,763	05/11/93	Lewis et al.			
QK		5,103,494	04/07/92	Mozer			
QL		4,594,000	06/10/86	Falk et al.			
QM		4,297,656	10/27/81	Pan			
QN		5,244,818	09/14/93	Jokers et al.			
QO		6,048,751	04/11/00	D'Asaro et al.			
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QT		6,271,619	08/07/01	Yamada et al.			
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RM		5,621,227	04/15/97	Joshi			
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	SZ	5,194,917	03/16/93	Regener			
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	TH	5,760,427	06/02/98	Onda			
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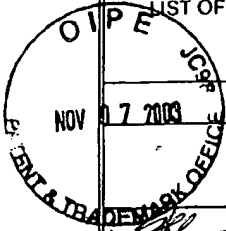
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AAE	0 607 435	07/27/94	EP	X	
AAF	1 001 468	05/17/00	EP	X	
AAG	0 514 018	11/19/92	EP	X	
AAH	0 999 600	05/10/00	EP	X	
AAI	1 319 311	06/04/70	Great Britain	X	
AAJ	5-291299	11/05/93	Japan w/English Abstract	X	
AAK	11-238683	08/31/99	Japan	X	
AAL	11-260835	09/24/99	Japan w/English Abstract	X	
AAM	HEI 2-391	01/05/90	Japan w/English Abstract	X	
AAN	5-48072	02/26/93	Japan w/English Abstract	X	
AAO	52-88354	07/23/77	Japan w/English Abstract	X	
AAP	54-134554	10/19/79	Japan w/English Abstract	X	
AAQ	55-87424	07/02/80	Japan w/English Abstract	X	
AAR	61-108187	05/26/86	Japan w/English Abstract	X	
AAS	6-232126	08/19/94	Japan	X	
AAT	6-291299	10/18/94	Japan w/English Abstract	X	
AAU	63-34994	02/15/88	Japan w/English Abstract	X	
AAV	63-131104	06/03/88	Japan w/English Abstract	X	
AAW	63-198365	08/17/88	Japan w/English Abstract	X	
AAX	10-321943	12/04/98	Japan	X	
AAZ	6-334168	12/02/94	Japan	X	
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ABB	WO 97/45827	12/04/97	WIPO		
ABC	WO 99/19546	04/22/99	WIPO		
ABD	WO 00/33363	06/08/00	WIPO		
ABE	WO 00/48239	08/17/00	WIPO		
ABF	WO 99/14797	03/25/99	WIPO		
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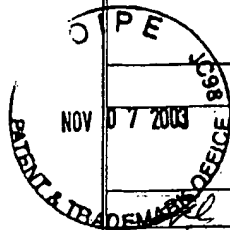
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BAF	WO 01/33585	05/10/01	WIPO		
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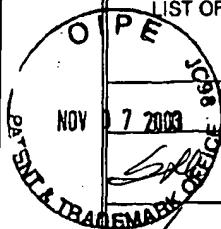
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CAG	WO 93/07647	04/15/93	WIPO			
CAH	2002-9366	01/11/02	Japan w/English Abstract			
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CCAA	Nakagawara et al., "Effects of Buffer Layers in Epitaxial Growth of SrTiO <sub>3</sub> Thin Film on Si(100), <i>J. Appl. Phys.</i> , 78 (12), December 15, 1995, pp. 7226-7230.		
CCAB	Suzuki et al., "A Proposal of Epitaxial Oxide Thin Film Structures For Future Oxide Electronics," <i>Materials Science and Engineering B41</i> , (1996), pp. 166-173.		
CCAC	W. F. Egelhoff et al., "Optimizing GMR Spin Valves: The Outlook for Improved Properties", 1998 <i>Int'l Non Volatile Memory Technology Conference</i> , pp. 34-37.		
CCAD	Wang et al., "Processing and Performance of Piezoelectric Films", Univ. Of MD, Wilcoxon Research Col. and Motorola Labs, May 11, 2000.		
CCAE	M. Rotter et al., "Nonlinear Acoustoelectric Interactions in GaAs/LiNbO <sub>3</sub> Structures", <i>Applied Physics Letters</i> , Vol. 75(7), August 16, 1999, pp. 965-967.		
CCAF	K. Sreenivas et al., "Surface Acoustic Wave Propagation on Lead Zirconate Titanate Thin Films," <i>Appl. Phys. Lett.</i> 52 (9), Feb. 29, 1998, pp. 709-711.		
CCAG	M. Rotter et al., "Single Chip Fused Hybrids for Acousto-Electric and Acousto-Optic Applications," 1997 <i>Applied Physics Letters</i> , Vol. 70(16), April 21, 1997, pp. 2097-2099.		
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CCAI	S. Mathews et al., "Ferroelectric Field Effect Transistor Based on Epitaxial Perovskite Heterostructures", <i>Science</i> , Vol. 276, April 11, 1997, pp. 238-240.		
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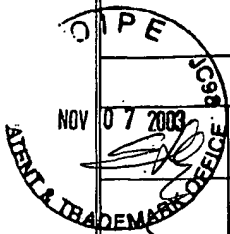
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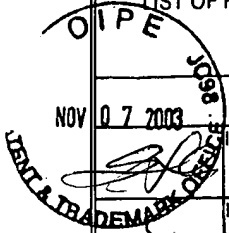
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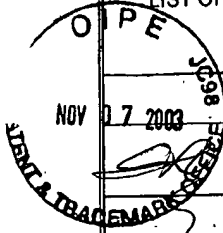
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KKA H	Mitsubishi Semiconductors Press Release (GaAs FET's) November 8, 1999 pp.1-2		
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KKA O			
KKA P			
KKA Q			
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<i>EX</i>	UT	5,528,209	06/18/96	Macdonald et al.			
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	UW	6,110,813	08/29/00	Ota et al.			
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	WA	5,905,571	05/18/99	Butler et al.			
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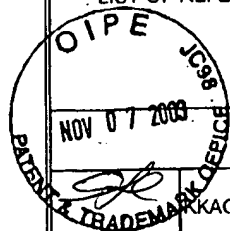
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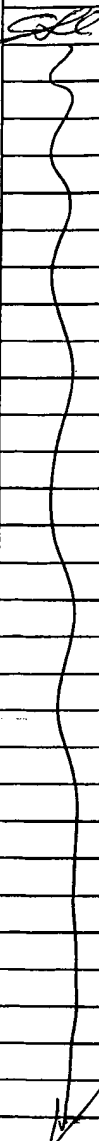
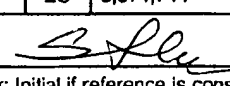
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CBE	5-232307	09/10/93	JAPAN W/ENGLISH ABSTRACT		
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CBH	EP 1 089 338	04/04/01	EUROPE		
CBI	01 294594	11/28/99	JAPAN (ABSTRACT)		
CBJ	05 221800	08/31/93	JAPAN (ABSTRACT)		
CBK	03-149882	11/07/89	JAPAN		
CBL	0 614 256	09/07/94	EUROPE		
CBM	0 054 442	11/22/00	EUROPE		
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CBO	W0 02/08806	01/31/02	WIPO		
CBP	W0 01/59837	08/16/01	WIPO		
CBQ	62-245205	10/26/87	JAPAN W/ENGLISH ABSTRACT		
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	XO	4,723,321	02/02/88	SALEH			
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	XQ	6,415,140 B1	07/02/02	BENJAMIN ET AL			
	XR	5,760,740	06/02/98	BLODGETT			
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	XT	4,876,218	10/24/89	PESSA ET AL			
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	XY	4,298,247	11/03/81	MICHELET ET AL			
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	YT	5,540,785	07/30/96	DENNARD ET AL			
	YU	5,997,638	12/07/99	COPEL ET AL			
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	ZB	5,313,058	05/17/94	FRIEDERICH ET AL			
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	ZD	5,919,522	07/06/99	BAUM ET AL			
	ZE	4,843,609	06/27/89	OHYA ET AL			
	ZF	4,626,878	12/02/86	KUWANO ET AL			
	ZG	4,525,871	06/25/85	FOYT ET AL			
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	ZI	6,059,895	05/09/00	CHU ET AL			
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	ZP	6,445,724 B2	09/03/02	ABELES			
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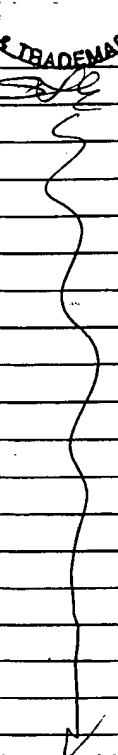
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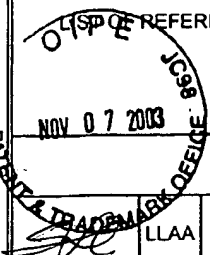
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TRADEMARK DES.		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION	
					YES	NO
	CCA	5-238894	09/17/93	JAPAN W/ENGLISH ABSTRACT		
	CCB	2 152 315	07/31/85	GREAT BRITAIN		
	CCC	2001-196892	07/19/01	JAPAN W/ENGLISH ABSTRACT		
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	LLAB	"Motorola Develops New Super-Fast Chip"; USA Today; Sept. 4, 2001					
	LLAC	Lori Valiga; "Motorola Lays GaAs on Si Wafer"; AsiaBizTech; Nov. 2001pp. 1-3					
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